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Team Nexperia



NPN resistor-equipped transistor; R1 = 2.2 kΩ, R2 = openRev. 1 — 12 June 2012Product data f

Product data sheet

Product profile 1.

1.1 General description

NPN Resistor-Equipped Transistor (RET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package.

PNP complement: PDTA123TMB.

1.2 Features and benefits

- 100 mA output current capability
- Reduces component count
- Built-in bias resistors
- Reduces pick and place costs

1.3 Applications

- Low-current peripheral driver
- Control of IC inputs

- Simplifies circuit design
- AEC-Q101 gualified
- Leadless ultra small SMD plastic package
- Low package height of 0.37 mm
- Replaces general-purpose transistors in digital applications
- Mobile applications

1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	50	V
lo	output current		-	-	100	mA
R1	bias resistor 1 (input)	T _{amb} = 25 °C	1.54	2.2	2.86	kΩ



NPN resistor-equipped transistor; R1 = 2.2 k Ω , R2 = open

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	I	input (base)		
2	G	GND (emitter)		3
3	0	output (collector)	2 Transparent top view SOT883B (DFN1006B-3)	1 2 sym012

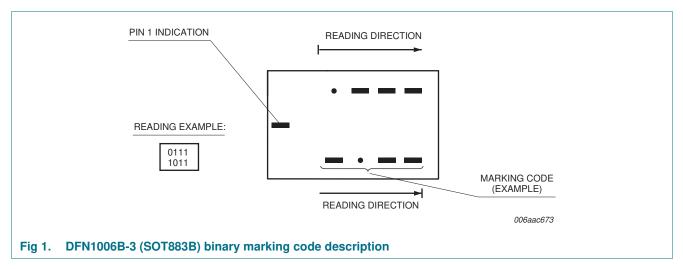
3. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
PDTC123TMB	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B				

4. Marking

Table 4.	Marking	codes
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Type number	Marking code
PDTC123TMB	0011 0101



NPN resistor-equipped transistor; R1 = 2.2 k Ω , R2 = open

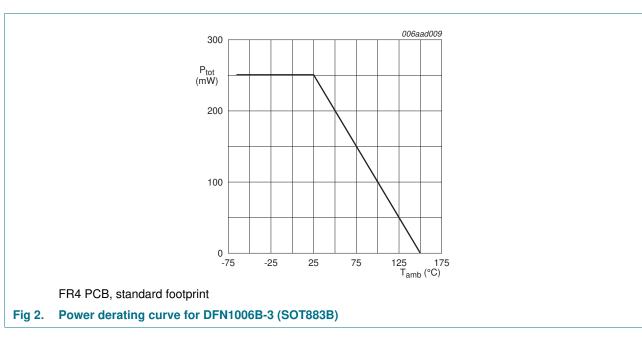
5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions		Min	Max	Unit
collector-base voltage	open emitter		-	50	V
collector-emitter voltage	open base		-	50	V
emitter-base voltage	open collector		-	5	V
output current			-	100	mA
peak collector current	pulsed; t _p ≤ 1 ms		-	100	mA
total power dissipation	T _{amb} ≤ 25 °C	<u>[1]</u>	-	250	mW
junction temperature			-	150	°C
ambient temperature			-65	150	°C
storage temperature			-65	150	°C
	collector-base voltagecollector-emitter voltageemitter-base voltageoutput currentpeak collector currenttotal power dissipationjunction temperatureambient temperature	collector-base voltageopen emittercollector-emitter voltageopen baseemitter-base voltageopen collectoroutput currentpulsed; $t_p \le 1$ mstotal power dissipation $T_{amb} \le 25 \text{ °C}$ junction temperatureambient temperature	collector-base voltageopen emittercollector-emitter voltageopen baseemitter-base voltageopen collectoroutput currentpulsed; $t_p \le 1$ mstotal power dissipation $T_{amb} \le 25$ °Cjunction temperatureIIambient temperature	collector-base voltageopen emitter-collector-emitter voltageopen base-emitter-base voltageopen collector-output currentpulsed; $t_p \le 1$ ms-peak collector currentpulsed; $t_p \le 1$ ms-total power dissipation $T_{amb} \le 25$ °C[1]junction temperature-ambient temperature-65	collector-base voltageopen emitter-50collector-emitter voltageopen base-50emitter-base voltageopen collector-5output current-100peak collector currentpulsed; $t_p \le 1$ ms-100total power dissipation $T_{amb} \le 25 ^{\circ}$ C11-250junction temperature-150ambient temperature-65150

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



6. Thermal characteristics

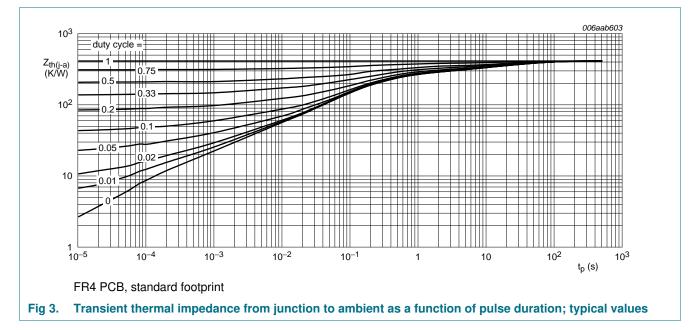
Table 6.	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	500	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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PDTC123TMB

NPN resistor-equipped transistor; R1 = 2.2 k Ω , R2 = open



7. Characteristics

Table 7. Characteristics

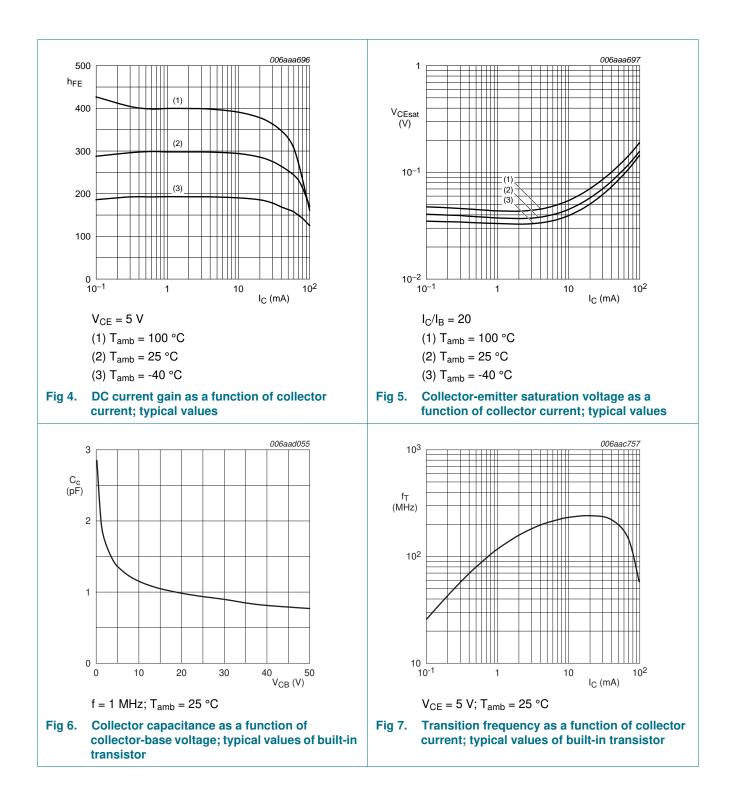
Parameter collector-base cut-off current collector-emitter cut-off current	V _{CB} = 50 V; I _E = 0 A; T _{amb} = 25 °C V_{CE} = 30 V; I _B = 0 A; T _{amb} = 25 °C V_{CE} = 30 V; I _B = 0 A; T _j = 150 °C		Min - -	Тур -	Max 100	Unit nA
current collector-emitter cut-off current	$V_{CE} = 30 \text{ V}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-		
current			-	-	1	
	V _{CE} = 30 V; I _B = 0 A; T _j = 150 °C				I	μΑ
	•		-	-	5	μA
emitter-base cut-off current	V_{EB} = 5 V; I_C = 0 A; T_{amb} = 25 °C		-	-	100	nA
DC current gain	V_{CE} = 5 V; I_{C} = 20 mA; T_{amb} = 25 °C		30	-	-	
collector-emitter aturation voltage	I_{C} = 10 mA; I_{B} = 0.5 mA; T_{amb} = 25 °C		-	-	150	mV
pias resistor 1 (input)	T _{amb} = 25 °C		1.54	2.2	2.86	kΩ
collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; T_{amb} = 25 \text{ °C}$		-	-	2.5	pF
ransition frequency	V_{CE} = 5 V; I _C = 10 mA; f = 100 MHz; T _{amb} = 25 °C	<u>[1]</u>	-	230	-	MH
	OC current gain ollector-emitter aturation voltage ias resistor 1 (input) ollector capacitance	DC current gain $V_{CE} = 5 \text{ V}; I_C = 20 \text{ mA}; T_{amb} = 25 \text{ °C}$ ollector-emitter aturation voltage $I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 \text{ °C}$ ias resistor 1 (input) $T_{amb} = 25 \text{ °C}$ ollector capacitance $V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; T_{amb} = 25 \text{ °C}$ ransition frequency $V_{CE} = 5 \text{ V}; I_C = 10 \text{ mA}; f = 100 \text{ MHz};$	DC current gain $V_{CE} = 5 \text{ V}; I_C = 20 \text{ mA}; T_{amb} = 25 \text{ °C}$ ollector-emitter aturation voltage $I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 \text{ °C}$ ias resistor 1 (input) $T_{amb} = 25 \text{ °C}$ ollector capacitance $V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; T_{amb} = 25 \text{ °C}$ ransition frequency $V_{CE} = 5 \text{ V}; I_C = 10 \text{ mA}; f = 100 \text{ MHz};$	DC current gain $V_{CE} = 5 \text{ V}; I_C = 20 \text{ mA}; T_{amb} = 25 \text{ °C}$ 30ollector-emitter aturation voltage $I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 \text{ °C}$ -ias resistor 1 (input) $T_{amb} = 25 \text{ °C}$ 1.54ollector capacitance $V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; T_{amb} = 25 \text{ °C}$ -ransition frequency $V_{CE} = 5 \text{ V}; I_C = 10 \text{ mA}; f = 100 \text{ MHz};$ 11	DC current gain $V_{CE} = 5 \text{ V}; \text{ I}_{C} = 20 \text{ mA}; \text{ T}_{amb} = 25 \text{ °C}$ 30-ollector-emitter aturation voltage $I_{C} = 10 \text{ mA}; \text{ I}_{B} = 0.5 \text{ mA}; \text{ T}_{amb} = 25 \text{ °C}$ ias resistor 1 (input) $\text{T}_{amb} = 25 \text{ °C}$ 1.542.2ollector capacitance $V_{CB} = 10 \text{ V}; \text{ I}_{E} = 0 \text{ A}; \text{ i}_{e} = 0 \text{ A};$ f = 1 MHz; $\text{T}_{amb} = 25 \text{ °C}$ ransition frequency $V_{CE} = 5 \text{ V}; \text{ I}_{C} = 10 \text{ mA}; \text{ f} = 100 \text{ MHz};$ 11-230	DC current gain $V_{CE} = 5 \text{ V}; \text{ I}_{C} = 20 \text{ mA}; \text{ T}_{amb} = 25 \text{ °C}$ 30 - - ollector-emitter $I_{C} = 10 \text{ mA}; \text{ I}_{B} = 0.5 \text{ mA}; \text{ T}_{amb} = 25 \text{ °C}$ - - 150 aturation voltage $I_{C} = 10 \text{ mA}; \text{ I}_{B} = 0.5 \text{ mA}; \text{ T}_{amb} = 25 \text{ °C}$ - - 150 vias resistor 1 (input) $T_{amb} = 25 \text{ °C}$ 1.54 2.2 2.86 ollector capacitance $V_{CB} = 10 \text{ V}; \text{ I}_{E} = 0 \text{ A}; \text{ i}_{e} = 0 \text{ A}; _{f} = 1 \text{ MHz}; \text{ T}_{amb} = 25 \text{ °C}$ - - 2.5 ransition frequency $V_{CE} = 5 \text{ V}; \text{ I}_{C} = 10 \text{ mA}; \text{ f} = 100 \text{ MHz};$ [1] - 230 -

[1] Characteristics of built-in transistor.

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PDTC123TMB

NPN resistor-equipped transistor; R1 = 2.2 kΩ, R2 = open



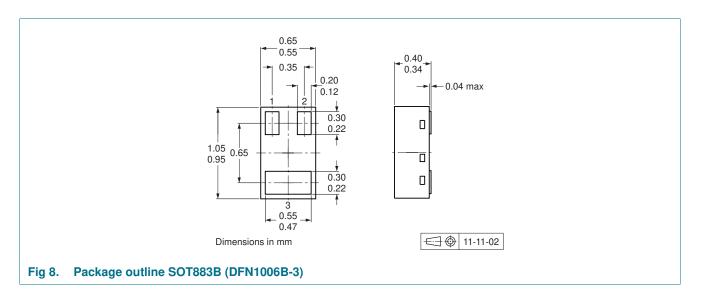
NPN resistor-equipped transistor; R1 = 2.2 k Ω , R2 = open

8. Test information

8.1 Quality information

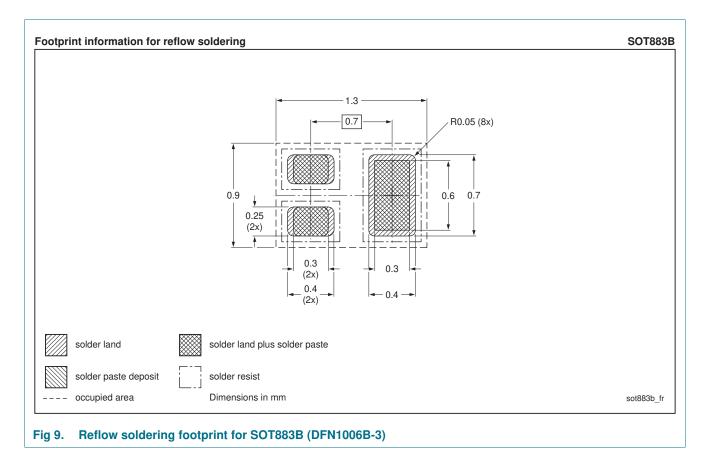
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

9. Package outline



NPN resistor-equipped transistor; R1 = 2.2 k Ω , R2 = open

10. Soldering



NPN resistor-equipped transistor; R1 = 2.2 k Ω , R2 = open

11. Revision history

Table 8. Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTC123TMB v.1	20120612	Product data sheet	-	-

NPN resistor-equipped transistor; $R1 = 2.2 \text{ k}\Omega$, R2 = open

12. Legal information

12.1 Data sheet status

Document status ^[1] ^[2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Product data sheet

PDTC123TMB

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NPN resistor-equipped transistor; R1 = 2.2 k Ω , R2 = open

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